

High Frequency Integrated Vacuum Electronics (HiFIVE) Industry Day Meeting



Background, Program Objectives and Structure

Mark J. Rosker
Program Manager
24 July 2007



Agenda



Introduction

1300-1330 Background, Program Objectives and Structure Mark Rosker (DARPA)

Area of Interest I: Vacuum Electronic Circuit Elements

1330-1350 High Current Density, Long-Life Cathode Dev Palmer (ARO)

1350-1410 High Aspect-Ratio Electron Beam
High Efficiency Interaction Structure Baruch Levush (NRL)

1410-1430 BREAK

1430-1440 High-Power MMIC Driver Alfred Hung (ARL)

1440-1455 High-Efficiency Thermal Management Jeff Calame (NRL)

Area of Interest II: Vacuum Electronic Circuit Design, Integration, and Demonstration

1455-1515 High Power Amplifier Design Baruch Levush (NRL)

1515-1530 Circuit Integration
Circuit Demonstration Jeff Calame (NRL)

1530-1545 BREAK

Wrap-Up

1545-1700 Questions & Answers Mark Rosker (DARPA)



DARPA Organization



Director, Tony Tether
Deputy Director, Bob Leheny

Tactical Technology

Steve Welby
Steve Walker

Air/Space/Land/Sea Platforms
Unmanned Systems
Space Operations
Laser Systems
Precision Strike

Information Exploitation

Bob Tenney
Mark Davis

Sensors
Exploitation Systems
Command & Control

Strategic Technology

Dave Honey
Larry Stotts/Brian Pierce

Space Sensors/Structures
Strategic & Tactical Networks
Information Assurance
Underground Facility Detection
& Characterization
Chem/Bio Defense
Maritime Operations

Defense Sciences

Brett Giroir
Barbara McQuiston

Physical Sciences
Materials
Biology
Mathematics
Human Effectiveness
Bio Warfare Defense

Information Processing Technology

Charlie Holland
Charles Morefield

Cognitive Systems
High Productivity Computing
Systems
Language Translation

Microsystems Technology

John Zolper
Dean Collins

Electronics
Photonics
MEMS
Algorithms
Integrated Microsystems

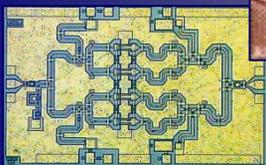


Microsystems Technology Office: Enabling Future Capability

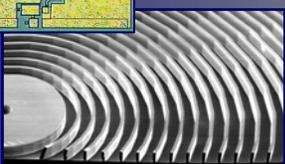


Sense

Microbolometer

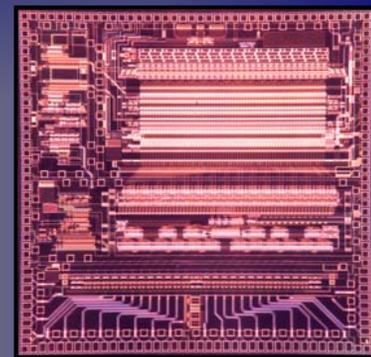


RF MMIC

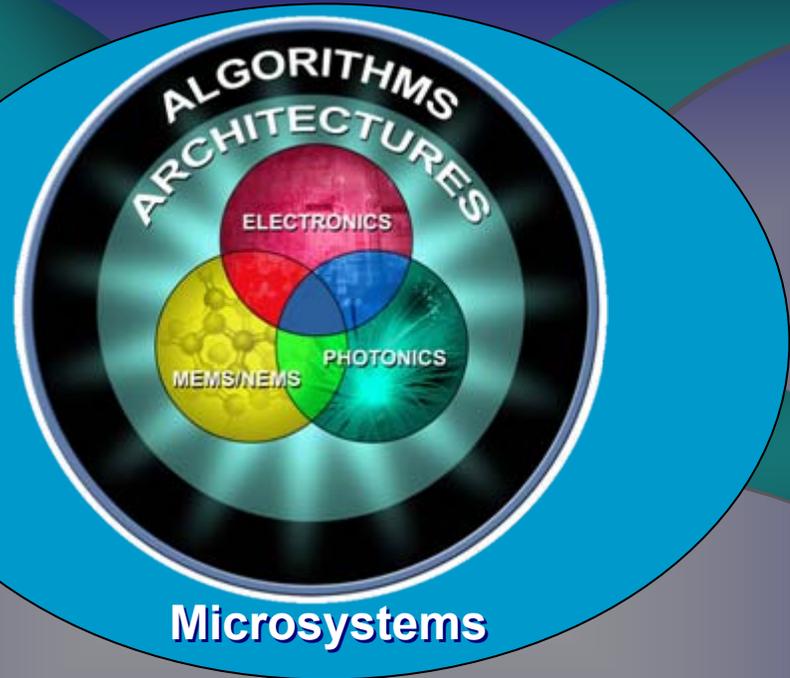


Micro Gas Analyzer

Process

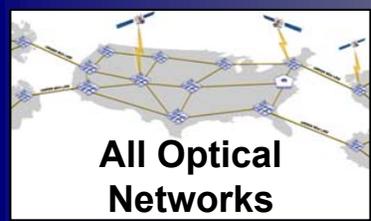


Digital Integrated Circuits

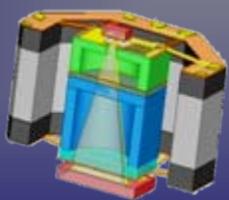


Microsystems

Communicate



All Optical Networks



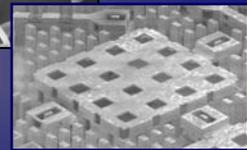
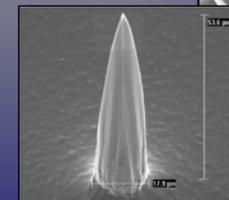
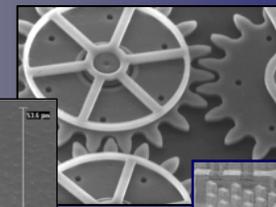
Chip Scale Atomic Clock

Energize



Adaptive Photonic Phase-Locked Elements

Actuate



MicroElectroMechanical devices



Welcome to HiFIVE



Legal Disclaimer



The DARPA / MTO HiFIVE program is not associated with any children's magazine

An Application Example: Something That Cannot be Done Today



Question #1

Is there an optimal RF frequency for an all-weather tactical comm link?

- “Optimal” = highest possible channel capacity
- Include antenna gain and atmosphere loss
- Assume RF components are available and performance (power, NF) is frequency invariant

Insight #1

Yes. The “upper MMW” (i.e., 200 – 300 GHz)

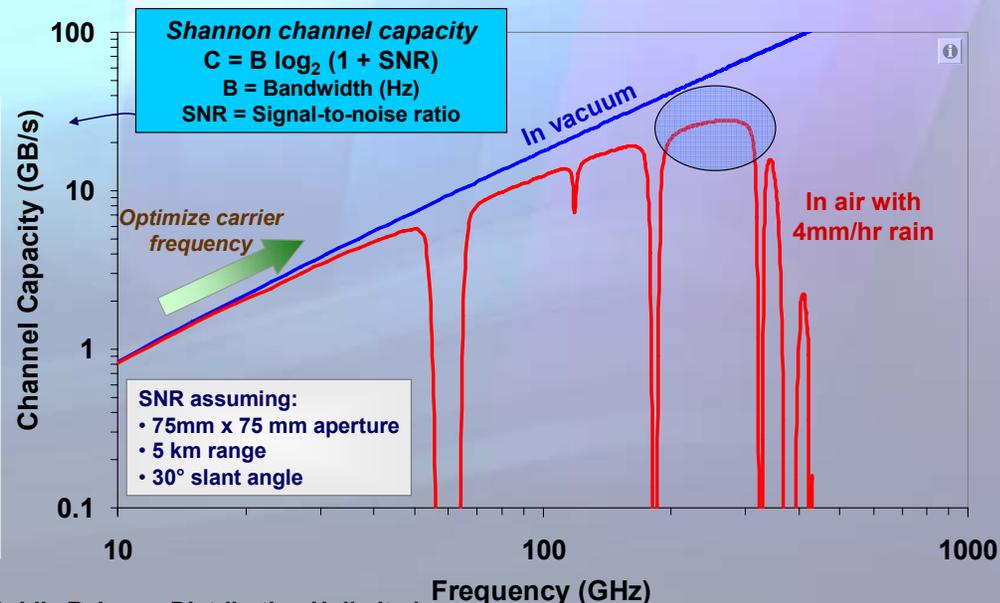
- Capacities can be comparable to SOA fibers!
- Even in relatively bad weather

But such a link requires a high power amplifier that doesn't exist today

The Challenge

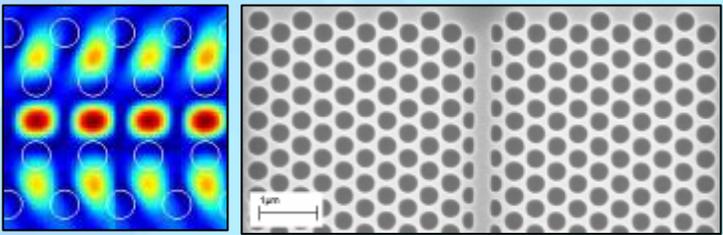
Can MTO make a “useable” power amplifier for the upper MMW?

- High power
 - Many 10's of W, not just a few W
- High bandwidth
 - Many GHz, not MHz
- Compact
 - Similar MPM's used now for such platforms



Question #2

Can the ideas of slow-light and EM (photonic) bandgap structures lead to RF device performance breakthroughs?



For optimal energy extraction, we must:

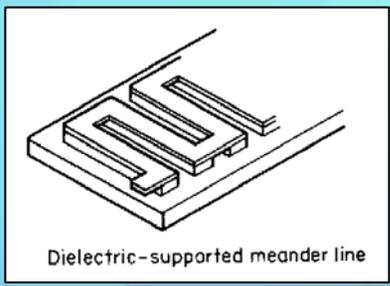
- Decrease the light (RF) wave velocity to increase the interaction time of the electron stream

$$V_{RF} \approx V_{\text{electrons}}$$

	Solid-State	Vacuum Electronics
$V_{\text{electrons}}$	low	high
Interaction Length	μm	mm

Insight #2

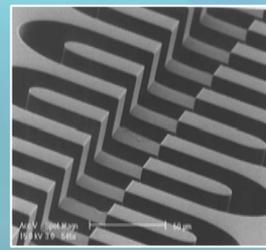
We've been here before!



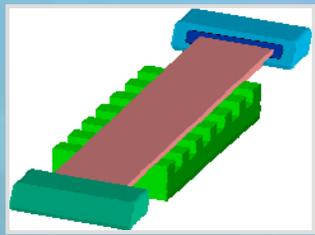
Vacuum electronics: the original slow-wave device

...but new approaches are now available.

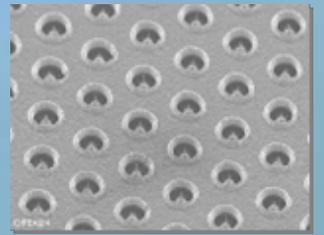
Si micromachining for high-frequency slow-wave structures



High aspect ratio* electron beams for slow-light structures



Cold beams



Can we use these new ideas to solve the "upper MMW" PA challenge?

* Ratio of total width of beam(s) to thickness

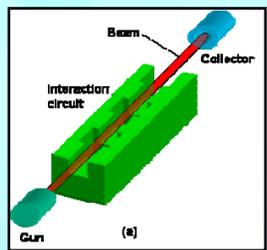
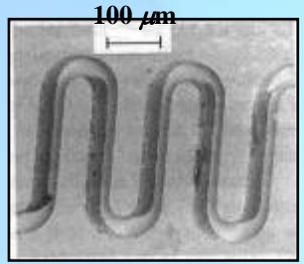
Can we go... *Back to the Future?*



Why didn't slow-wave vacuum electronics lead to a compact, high power-BW upper MMW power amplifier ?

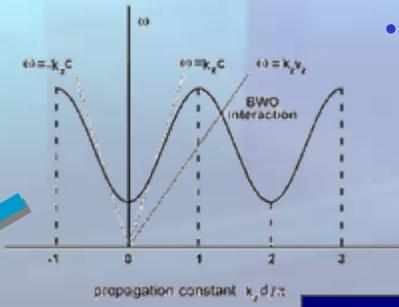
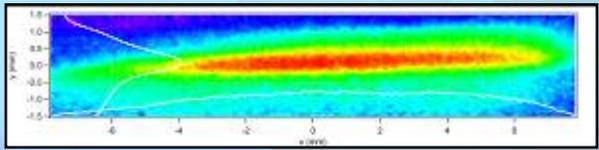


- **Couldn't build it:** Required slow-wave structure tolerances beyond conventional (wire EDM) machining
→ Better fabrication method

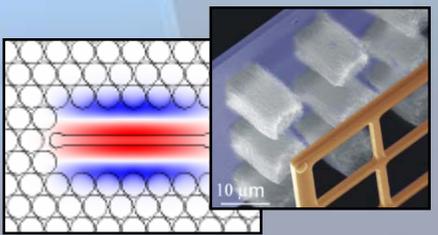


- **Couldn't extract enough power from it:** Power out from slow-wave structure scales $\sim Nf^{-8/3}$
→ High aspect ratio (N) e-beam*

* Ratio of total width of beam(s) to thickness



- **Couldn't keep velocity match:** Bandwidth limited by electron velocity spread, mode dispersion, and energy transfer
→ Beam cooling
→ Reduced mode dispersion
→ Tapering



Microfabrication technology is our time machine!

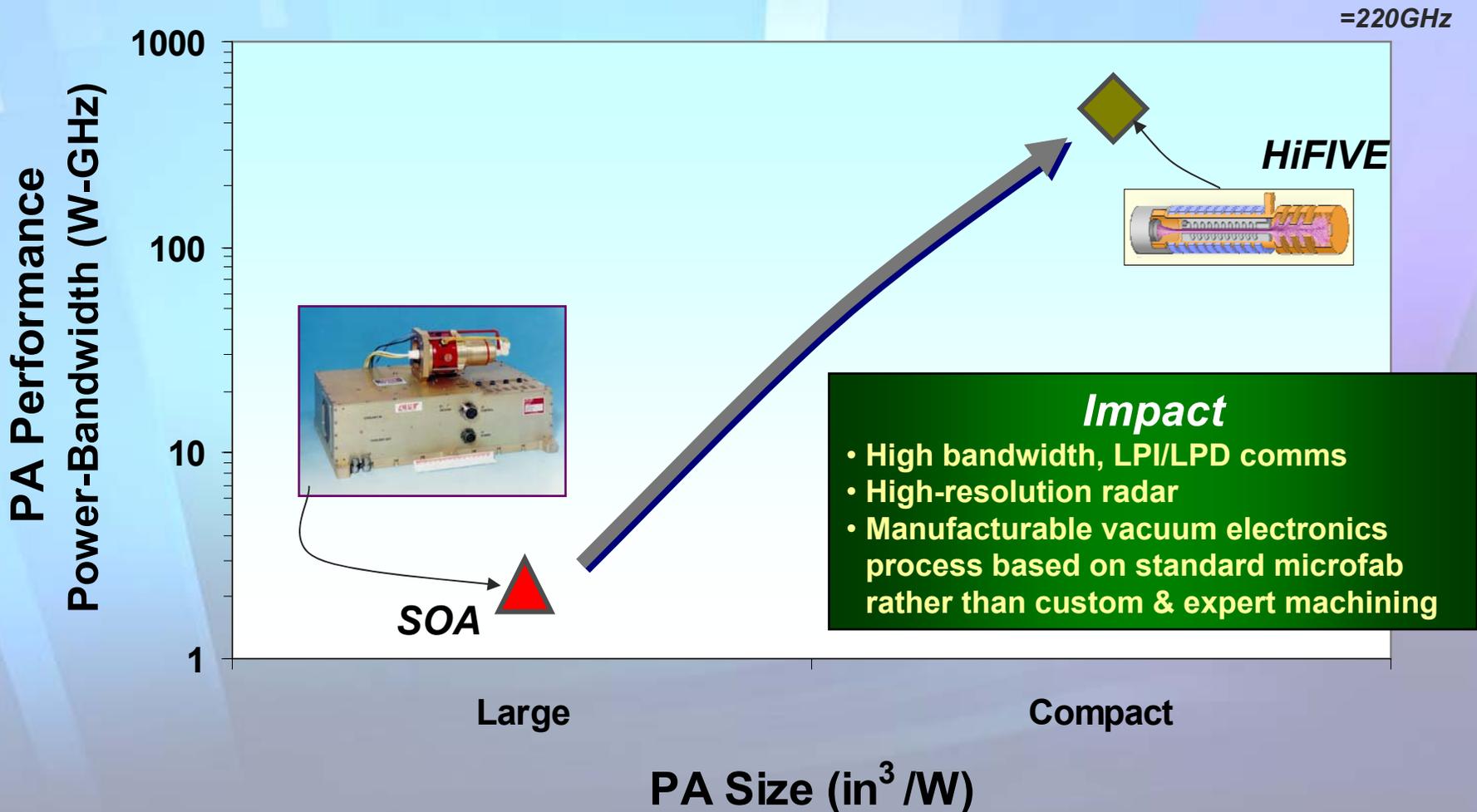


High Frequency Integrated Vacuum Electronics (HiFIVE)

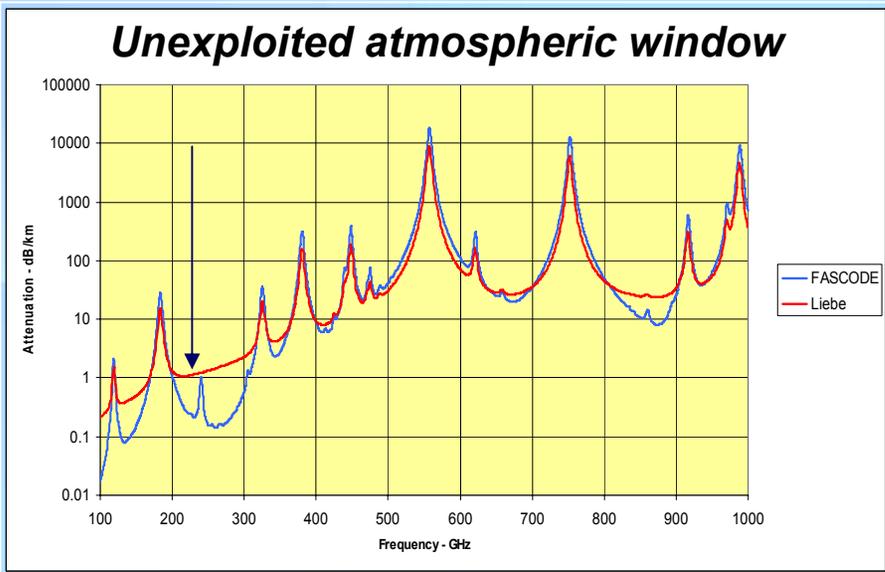


Program Objective

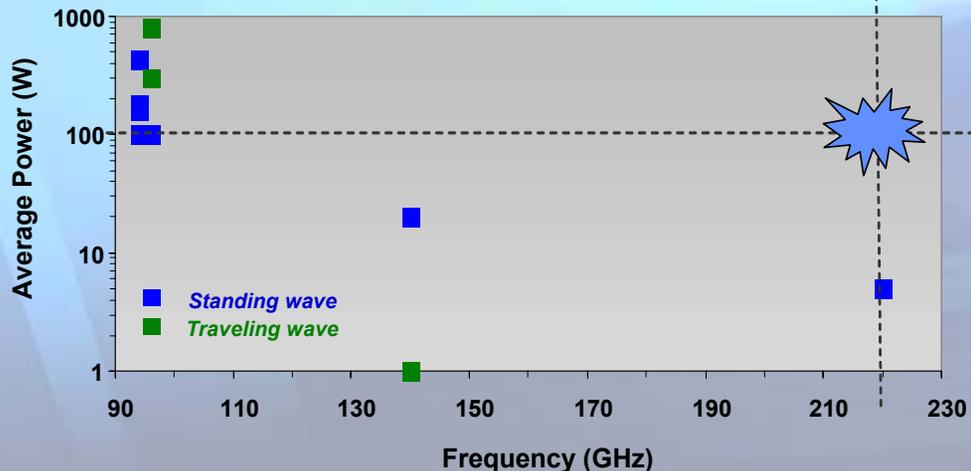
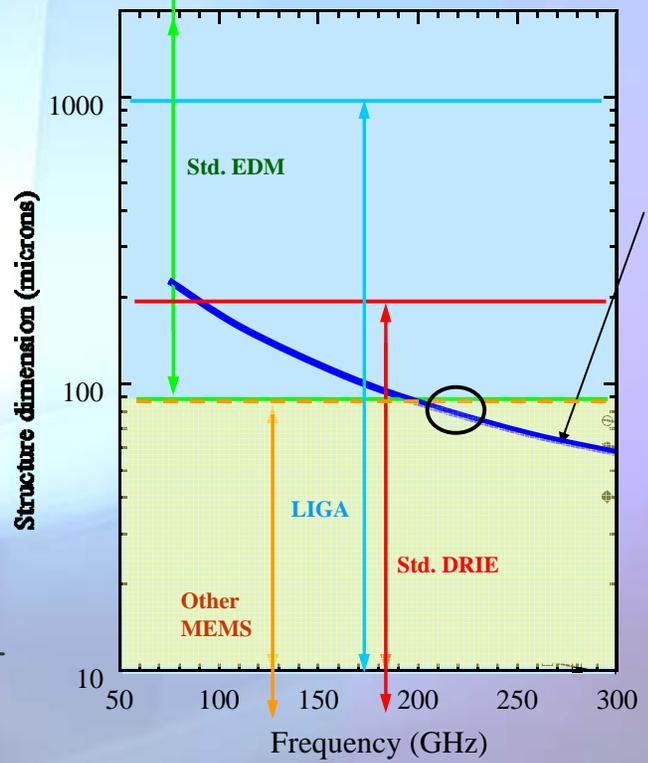
Demonstrate a compact, high-bandwidth, high-power “upper millimeter-wave” amplifier



Why 220GHz?

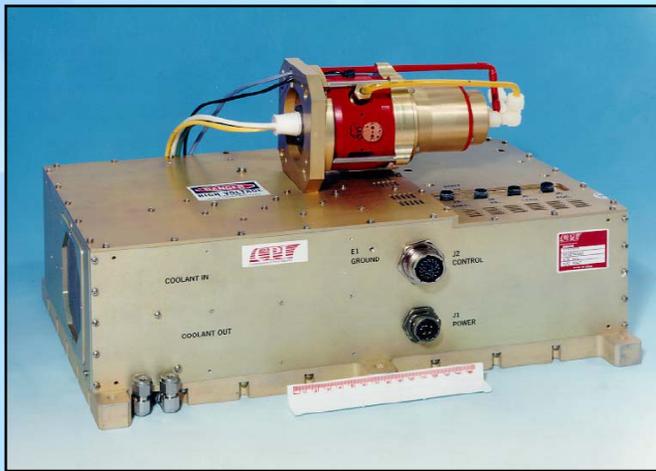


Microfab Required

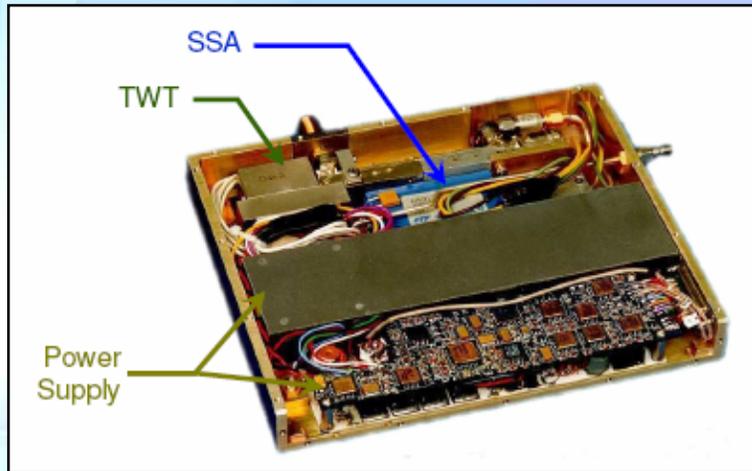


What Is Compact?

PA size can be dominated by the high voltage power supply



Substantial engineering has miniaturized & flight qualified HV power supplies to ~20kV

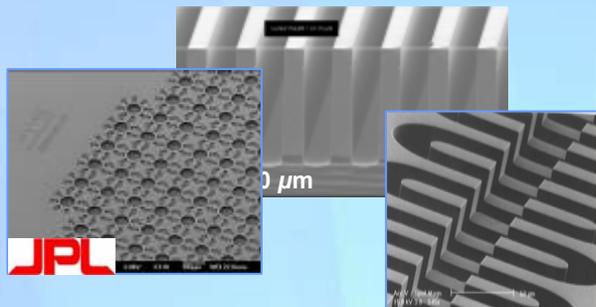


Fixed upper limit on circuit magnetic field B_{max} due to permanent magnet technology (~ 11 kG)
Practical upper limit on beam voltage ~ 20 kV

In HiFIVE, we expect $V < 20kV$ and $B_{max} < 11kG$

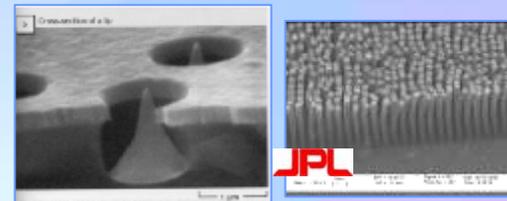
Why Now? Some HiFIVE Enablers

Micromachining Approaches Achieving Fine Surface Smoothness and High Aspect Ratio



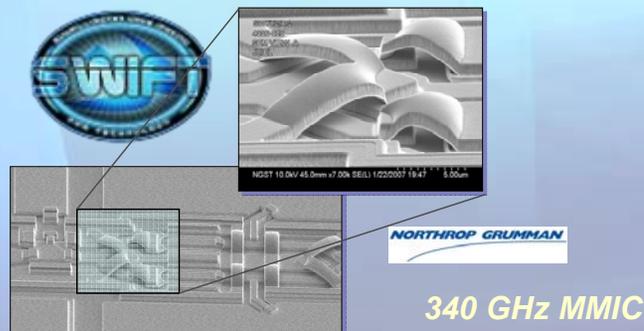
- **High precision machining of interaction structures**
- **Structures susceptible to outgassing adsorption**
- **Depth of structure difficult for many techniques**

Novel Field Emitter Array Cathodes with Improved Current Density



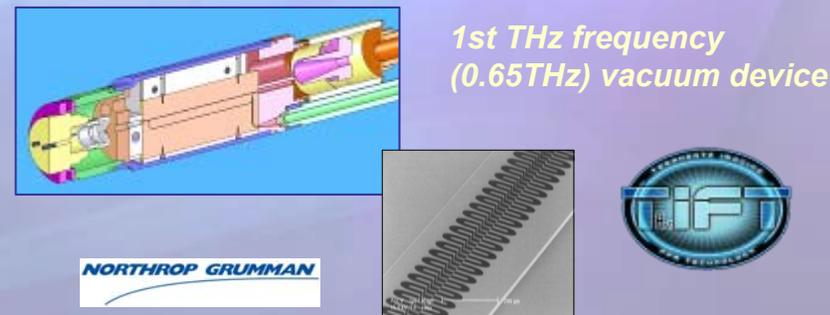
- **Compact and efficient**
- **Very short lifetimes**
- **Further increase in current densities needed**

High Frequency MMIC Process



- **Frequency of operation now well beyond 220GHz**
- **Need to increase power**
- **Integrating the device is difficult (high loss)**

THz Frequency TWTA Demo

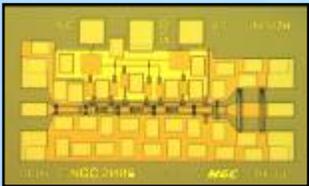


- **High precision machining at frequency**
- **Round beam**
- **Lower frequency structure more difficult**

Technical Challenges

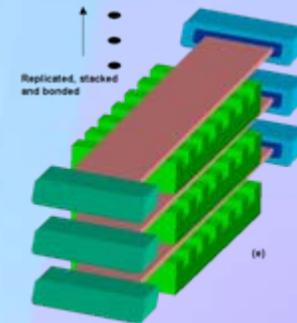
High Power MMIC Driver

- Accommodate relatively low VE gain at 220 GHz



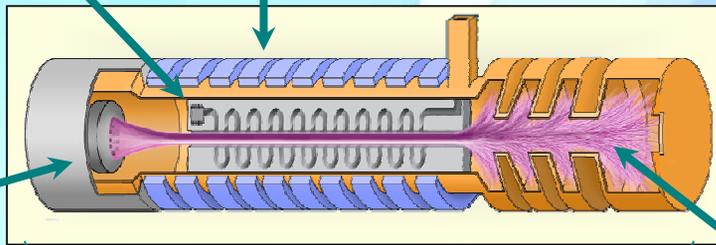
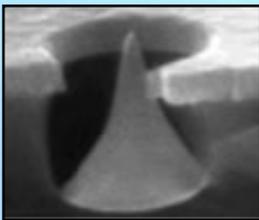
High Aspect-Ratio Devices

- High efficiency interaction structures
- Single vs. multi-beam topologies
- Magnetic compression to achieve high aspect ratio beam (N~100)
- Mitigation of parasitic oscillations



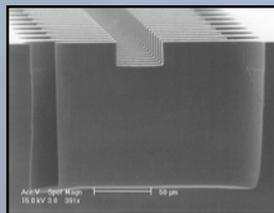
High Current Density, Long Life Cathodes

- High unfocused current density (~100A/cm²)
- Life > 10³ hrs



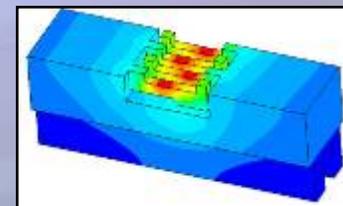
High Precision Micromachined Fabrication and Integration

- Achieve required smoothness & aspect ratio
- Material/technology/process compatibility
- Heterogeneous integration
- Maintain high vacuum



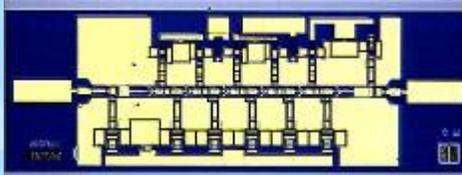
High Efficiency Thermal Management

- Mode confinement / reduction of beam interception
- Aggressive thermal management (mat'ls and structures)



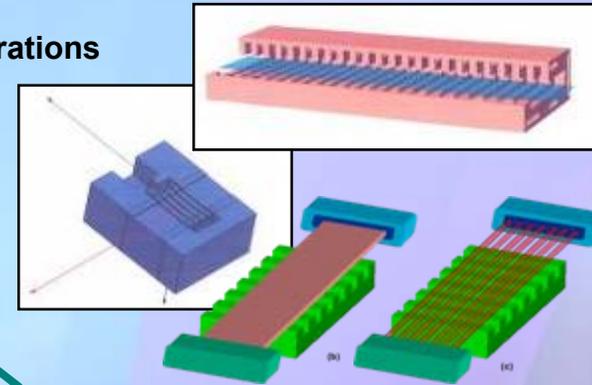
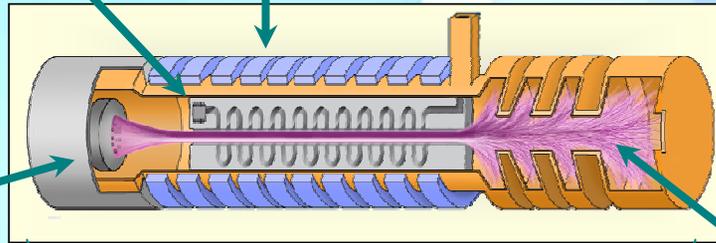
High Power MMIC Driver

- InP HEMT or HBT MMIC



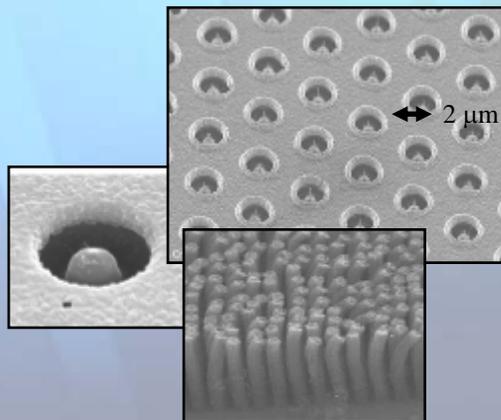
High Aspect-Ratio Devices

- High efficiency interaction structures
- Sheet beam EIK
- Sheet beam coupled cavity traveling wave
- Helix
- Stacked multi-beam configurations



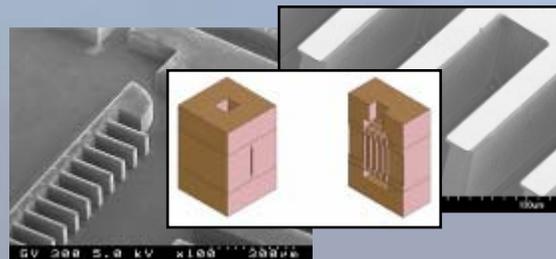
High Current Density, Long Life Cathodes

- Field emitters (cold cathodes)
- Carbon nanotube bundles
- Scandates



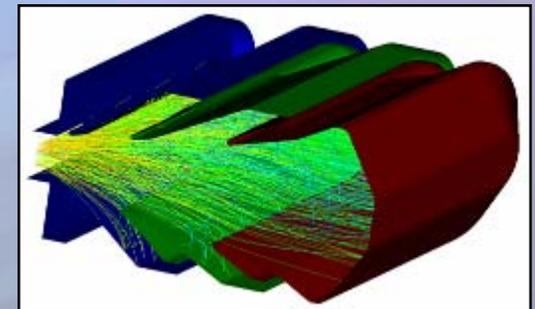
High Precision Micromachined Fabrication and Integration

- DRIE
- LIGA
- CVD diamond with metallization
- 3D-MERFS

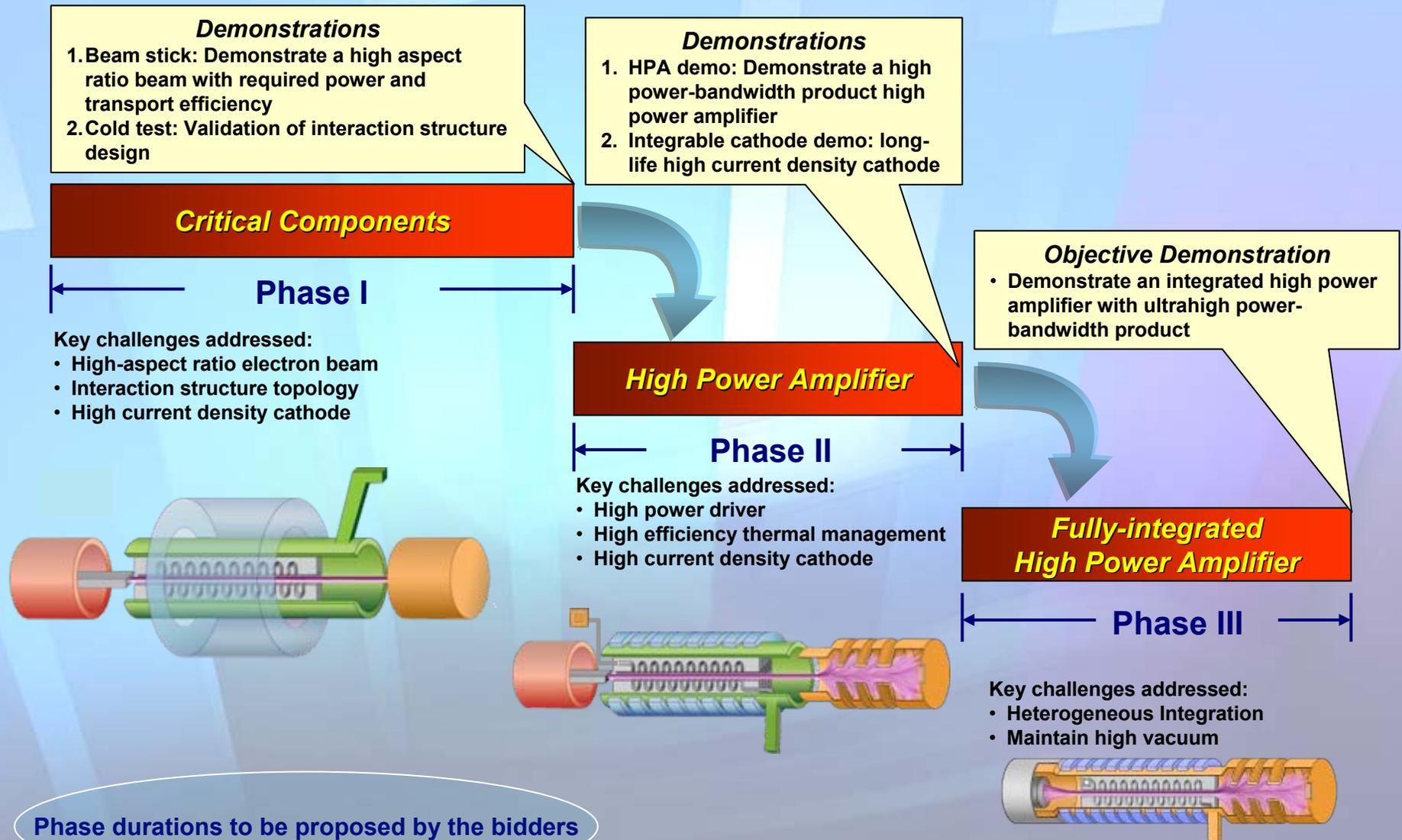


High Efficiency Thermal Management

- Multi-stage depressed collector
- Microchannel cooling



Program Schedule





Program Metrics



Metric	Unit	SOA	Phase I	Phase II	Phase III
Go/No Go Metrics					
Beam voltage	kV		20		
Cathode current density ⁽¹⁾	A/cm ²	10	750		
Beam aspect ratio ⁽²⁾		1	25		
Beam transport efficiency	%		95		
Center frequency accuracy	%		<u>+2</u>		
P _{out} ⁽³⁾	W	5 ⁽⁴⁾		50	50
Bandwidth	GHz	0.4 ⁽⁴⁾		5	5
Power-bandwidth product	W*GHz	2 ⁽⁴⁾		250	500
Efficiency ⁽⁵⁾	%	<1%		5%	5%
Total current ⁽⁶⁾	mA	100		250 ⁽⁷⁾	250 ⁽⁸⁾
Other Metrics					
Spectral purity ⁽⁹⁾	dBc			-50	-50
Driver output power ⁽³⁾	mW	50 ⁽⁴⁾		50	50

- (1) Measured in beam stick; pulsed
- (2) Defined as sum of the width of all beams/thickness of beams
- (3) Average power at 220GHz, measured external to device
- (4) Projected performance at 220GHz; research device
- (5) Total wallplug efficiency

- (6) Measured at cathode surface, for 1000 hours life
- (7) As a component
- (8) Integrated into HPA
- (9) Measured 250kHz from carrier



Demonstrations



Metric	Unit	Phase I		Phase II		Phase III	
		Value	Demo	Value	Demo	Value	Demo
Go/No-Go Metrics							
Beam voltage	kV	20	1A				
Circuit current density ⁽¹⁾	A/cm ²	750	1A				
Beam aspect-ratio ⁽²⁾		25	1A				
Beam transport efficiency	%	95	1A				
Center frequency accuracy	%	±2	1B				
P _{out} ⁽³⁾	W			50	2A	50	3
Bandwidth	GHz			5	2A	5	3
Power-bandwidth product	W*GHz			250	2A	500	3
Efficiency ⁽⁴⁾	%			5%	2A	5%	3
Total current ⁽⁵⁾	mA			250 ⁽⁶⁾	2B	250 ⁽⁷⁾	3
Additional Metrics							
Spectral purity ⁽⁸⁾	dBc			-50	2A	-50	3
Driver output power ⁽³⁾	mW			50	2A	50	3



Advanced Studies



“The HiFIVE program has two Technical Areas of Interest. Bidders are requested to address both technical areas of interest in a comprehensive manner. However, highly innovative advanced studies in one or more of these technical areas by individual investigator or small groups may also be considered. A bidder who is proposing such an advanced study should clearly identify it as such, should present its (limited) objectives and metrics (see below), and should explain the relevance of the work to the overall program goals...”

More Likely to Be of Interest

- **Efforts that could improve the likelihood that the integrated (“main”) performers will be successful, by (for example)...**
 - Providing a useful new tool (e.g., design) beyond what it already available
 - Providing a needed capability (e.g., test) beyond what it already available
 - Mitigating downstream risks (e.g., in a future Phase)
 - There should exist a path by which technology will transition to the main performers
- **Efforts that could extend the technology developed by the main performers by (for example)...**
 - Facilitating transition
 - Solving “adjacent” challenges
 - There should be a clear explanation of how

Less Likely to Be of Interest

- **Efforts that attempt to solve a subset of the same technical challenges the main performers are simultaneously addressing (“Provide a partial solution to the problem”)**
- **Proposals that may merely “improve” the choice of demonstration circuits**

A proposal with metrics and/or demo circuits that are mainly the same as those described in the BAA probably isn’t an advanced study



Some BAA Excepts



- *A team approach is strongly encouraged.*
- *Each phase will culminate in specified demonstration(s) that will serve to validate that the goals of that phase have been achieved and that the performer has met the GNG metrics.*
- *Offerors should describe, in detail, within their proposal how they plan to evaluate the demonstration circuits to validate that they have met the GNG requirements.*
- *Table 1 shows the minimal set of GNG metric values which must be achieved by the conclusion of each phase. Offerors may, at their option, propose a more ambitious and/or detailed set of GNG metrics.*
- *The primary deliverables for the HiFIVE program will be the experimental demonstrations described in Section 3 above...The performer should deliver the demonstration devices (or copies thereof) along with a description of the test equipment and test procedures necessary to enable the Government to conduct independent test and evaluation.*
- *Proposers must define a realistic schedule and budget that meets the milestone and deliverable requirements.*



Some Important Dates



- **Proposal abstract due** 22 Aug 2007
- **Feedback from DARPA** 24 Sep 2007*
- **Full proposal due** 23 Oct 2007

* Approx.

Discussion with the DARPA PM are allowed & encouraged



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Wrap-Up

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